

< C band internally matched power GaAs FET >

MGFC42V4450

4.4 - 5.0 GHz BAND / 16W

DESCRIPTION

The MGFC42V4450 is an internally impedance-matched GaAs power FET especially designed for use in 4.4 – 5.0 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

• High output power

P1dB=16W (TYP.) @f=4.4 - 5.0GHz

• High power gain

GLP=12dB (TYP.) @f=4.4 - 5.0GHz

High power added efficiency

P.A.E.=32% (TYP.) @f=4.4 - 5.0GHz

• Low distortion [item -51]

IM3=-45dBc (TYP.) @Po=31dBm S.C.L

APPLICATION

• item 01: 4.4 – 5.0 GHz band power amplifier

• item 51: 4.4 – 5.0 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=4.5A Refer to Bias Procedure • RG=25ohm

Absolute maximum ratings (Ta=25°C)

rain breakdown voltage	-15	V
auraa braalidaura valtaaa		
ource breakdown voltage	-15	٧
rent	15	Α
gate current	-40	mA
gate current	84	mA
er dissipation	78.9	W
mperature	175	°C
emperature	-65 to +175	°C
	rent gate current gate current er dissipation emperature emperature	rent 15 gate current -40 gate current 84 er dissipation 78.9 emperature 175

1 : Tc=25°C

OUTLINE DRAWING Unit: millimeters (inches) 24+/-0.3 R1.25 R1.2 (2) (3) 20.4+/-0.2 13.4 (1): GATE (2): SOURCE (FLANGE) **GF-18** (3): DRAIN

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Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	9	12	Α
gm	Transconductance	VDS=3V,ID=4.4A	-	4	i	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=80mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=4.5A	41.5	42.5	i	dBm
GLP	Linear Power Gain	f=4.4 - 5.0GHz	9	12	-	dB
ID	Drain current		-	5.4	ı	Α
P.A.E.	Power added efficiency		-	32	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	=	1.9	°C/W

^{*2 :}item -51 ,2 tone test,Po=31dBm Single Carrier Level ,f=5.0GHz,delta f=10MHz

^{*3:} Channel-case

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